Nanoscale Conductivity Imaging of Correlated Electronic States in WSe₂/WS₂ Moiré Superlattices

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Abstract

We report the nanoscale conductivity imaging of correlated electronic states in angle-aligned WSe₂/WS₂ heterostructures using microwave impedance microscopy. The noncontact microwave probe allows us to observe the Mott insulating state with one hole per moiré unit cell that persists for temperatures up to 150 K, consistent with other characterization techniques. In addition, we identify for the first time a Mott insulating state at one electron per moiré unit cell. Appreciable inhomogeneity of the correlated states is directly visualized in the hetero-bilayer region, indicative of local disorders in the moiré superlattice potential or electrostatic doping. Our work provides important insights on 2D moiré systems down to the microscopic level.

The vertical stacking of two-dimensional (2D) materials with similar lattice constants at small twist angles produces long-wavelength moiré superlattices, which can substantially modify the electronic structures of individual layers¹⁻³. As exemplified by the groundbreaking experiments⁴⁻⁶ and subsequent works⁷⁻¹², a plethora of exotic behaviors such as Mott insulating states⁴⁻⁹, superconductivity^{5,7-9}, magnetic phases¹⁰⁻¹², and quantum anomalous Hall effect¹² have been reported on twisted bilayer graphene near the magic angle and trilayer graphene/boron nitride moiré superlattices. Moiré systems composed of transition metal dichalcogenide (TMD) heterostructures offer a complementary and equally important material platform to investigate the rich many-body phenomena¹³. Because of the strong spin-orbit coupling, only two-fold degeneracy remains in the TMD-based moiré systems, giving rise to an ideal playground to simulate the Mott-Hubbard physics in 2D triangular lattices¹³⁻¹⁸. To date, evidence of charge ordering and correlated states at partial moiré band fillings has been reported in both homo-bilayer¹⁶ and hetero-bilayer TMD superlattices^{17,18}, with many other novel electronic states expected to emerge¹⁹.

A notable experimental challenge in the investigation of TMD moiré superlattices lies in the large metal-semiconductor contact resistances, especially at the low-density regime where correlation effects manifest themselves. As a result, optical measurements such as reflectance¹⁷ and optically detected resistance and capacitance (ODRC)¹⁸ are preferred over traditional transport techniques. A non-contact method that directly measures the electrical conductivity is therefore desirable to understand the insulating nature of Mott-like states in these materials. Moreover, as electrical properties of moiré superlattices are highly sensitive to the local atomic arrangement and disordered effects in the 2D sheets²⁰⁻²⁴, it is imperative to study the correlation physics in a spatially resolved manner. In this work, we report the optical study and nanoscale conductivity imaging of angle-aligned WSe₂/WS₂ moiré hetero-bilayers by combining ODRC and microwave impedance microscopy (MIM) on the same devices. At sufficiently low temperatures, while the overall gate dependence of local conductivity in the monolayer regions are described by the ambipolar field effect, pronounced resistivity peaks on both electron and hole sides are observed in the superlattice area at certain moiré band fillings. The resistivity peak at one hole per lattice site is consistent with the Mott insulator state reported previously^{17, 18}. Resistivity peak at one electron per lattice site, on the other hand, is reported for the first time, which indicates that the Mott state is also present in electron-doped WS₂/WSe₂ moiré systems. In addition, the microwave images show clear spatial inhomogeneity of the correlated states, presumably due to local disorders in the moiré potential or electrostatic doping. Our results provide important insights for improving the quality of TMD moiré superlattices towards new discoveries in these fascinating material systems.

The samples in our study are WSe₂/WS₂ hetero-bilayers, which are encapsulated by top and bottom hexagonal boron nitride (hBN) dielectrics, as illustrated in Fig. 1a. Few-layer graphene (FLG) layers are used as the gate and contact electrodes (details in Supplementary Information S1). The twist angle between the two monolayers is $\theta \sim 60^{\circ}$ (Supplementary Information S2), resulting in a moiré superlattice constant $L_M = a/\sqrt{\delta^2 + (\pi/3 - \theta)^2} \sim 8$ nm, where $\delta \sim 4\%$ is the lattice mismatch between monolayer WSe₂ (a = 0.328 nm) and WS₂ flakes. As seen in the optical image in Fig. 1b, half of the heterostructure (Region I) is covered by the top graphene layer, whereas the other half (Region II) is not. Significant inhomogeneity due to trapped bubbles are observed in this heterostructure devices. The optical absorption spectrum on Region II (Fig. 1c) shows that the WSe₂ A exciton is split into three peaks, indicative of the presence of the moiré potential²⁵ (more data in Supplementary Information S3).

To study the correlated electronic behavior in the sample, we perform ODRC measurements at 10 K. A d.c. voltage applied to the top gate (V_{tg}) is used to tune the carrier concentration in region I, and an a.c. voltage $(\Delta \tilde{V})$ induces charge redistribution between regions I and II. A probe laser in resonance with the lowest-energy WSe₂ exciton peak is used to measure charge flow in the sample¹⁸ (details in Supplementary Information S4). Fig. 1d shows the measured ODRC signals as a function of V_{tg} at three excitation frequencies. Consistent with the previous report^{17,18}, a prominent dip in the change of optical contrast is observed at $V_{tg} \sim -1.37$ V, corresponding to a filling factor $n/n_0 = -1$ or one hole per moiré unit cell (*n* represents the charge unit cell). In addition to this Mott state, a satellite dip also appears at factional filling $n/n_0 = -1/3$.



FIG. 1. (a) Schematic of the gated WSe₂/WS₂ superlattice device structure. The thicknesses of top and bottom hBN are 11 nm and 16 nm, respectively. (b) Optical microscopy image of the heterostructure device. The WSe₂, WS₂ monolayer flakes, FLG contact and top gate are outlined in green, orange, white, and black, respectively. (c) Optical absorption spectrum in Region II of the heterostructure in (b). The three peaks indicated by dashed lines are due to splitting of the WSe₂ A exciton, which is indicative of intra-layer moiré excitons in the WSe₂/WS₂ superlattice. (d) ODRC signals at two different a.c. excitation frequencies as a function of the top gate voltage and filling factors. The dashed line denotes the charge-neutral point (~ -0.3V) and the shaded areas correspond to the Mott insulator state at $n/n_0 = -1$ and correlated insulating state at -1/3. The inset illustrates the Mott insulator state with one hole per moiré unit cell.

The nanoscale conductivity of the moiré superlattice device is studied by microwave impedance microscopy (MIM)²⁶, a versatile technique for imaging the spatial uniformity of electrical properties in advanced materials²⁷⁻³⁰. As shown in Fig. 2a, a microwave signal (~ 10 μ W at 1 GHz) is delivered to a chemically etched tungsten tip, which is mounted on a quartz tuning fork (TF) for distance feedback^{31,32}. The two MIM output signals, proportional to the imaginary (MIM-Im) and real (MIM-Re) parts of the tip-sample admittance, are demodulated at the TF resonant frequency (~ 37 kHz). The spatial resolution is on the order of 100 nm, which is comparable to the tip diameter, as shown in the scanning electron microscopy (SEM) image in Fig.

2a. The MIM response to the sheet conductance of a buried 2D layer can be modeled by finite element analysis (FEA)²⁶. Fig. 2b shows the simulated MIM result as a function of the 2D conductance σ of, e.g., the WS₂ monolayer in both semi-log (main plot) and linear (inset) scales. Note that the MIM-Im signal increases monotonically with increasing σ , whereas MIM-Re peaks at $\sigma \sim 10^{-7}$ S·sq (see details in Supplementary Information S5). For comparison, the measured room-temperature MIM signals as a function of the back-gate voltage (V_{bg}) in the monolayer WS₂ region are shown in Fig. 2c. Below a threshold voltage of ~ 0.3 V, MIM signals in both channels are negligible, indicating the absence of mobile carriers when the Fermi level is inside the semiconducting gap. For $V_{bg} > 0.3$ V, the electrostatic doping occurs, as evidenced by the increase of MIM signals. The close resemblance between the simulated (Fig. 2b inset) and measured (Fig. 2c) results suggests that the device behaves as a regular back-gated field-effect transistor (FET). For simplicity, we will in the following only present the MIM-Im data because of its monotonic relationship with respect to the local conductance. A complete set of the MIM data are found in Supplementary Information S6. Similar results on a different WSe₂/WS₂ sample with near-0° twist angle are also included in Supplementary Information S7.



FIG. 2. (a) Schematic diagram of the TF-MIM measurements on the WSe₂/WS₂ hetero-bilayer device. The inset shows the SEM image of the etched tungsten tip. (b) FEA simulated MIM signals as a function of the sheet conductance of the buried TMD layers. The inset shows the same plot in the linear scale. (c) Measured room-temperature MIM signals on the WS₂ monolayer (orange star in **a**) as a function of the back-gate voltage. The black dash-dotted line indicates the charge-neutral point for electrons at ~ 0.3 V, where the Fermi level resides at the conduction band minimum (inset).

The cryogenic MIM experiment is carried out in a helium-flow cryostat with a base temperature ~ 20 K. Fig. 3a displays the sample topography taken by the TF feedback, where some surface impurities or air bubbles are clearly visible. The simultaneously acquired MIM-Im image at $V_{bg} = 0$ V and T = 24 K (Fig. 3b) shows that only the contact and top-gate FLG regions are

conductive. Strikingly, while the individual TMD layers and the heterostructure (HS) region are both highly insulating at zero V_{bg} , they exhibit very different gate dependences. As seen in the inset of Fig. 3b, monolayer WSe₂ is conductive at $V_{bg} = -2$ V due to the electrostatic doping of holes. The HS region, however, is strongly insulating. Such an unusual behavior of the WSe₂/WS₂ bilayer is beyond the simple description of a back-gated FET and worth further investigation.

Since the vertically stacked layers are relatively fragile and could be easily damaged by repeated scans, we focus on point measurements for systematic studies of the gate dependence. Fig. 3c shows the MIM-Im response on three points (WS₂, WSe₂, and HS) indicated in Fig. 3a when V_{bg} is swept from -2.7 to 2.7 V. The ambipolar-like FET behavior is observed in both monolayers. We notice that the WS₂ layer is much more difficult to turn on with hole doping, similar to previous FET studies³³⁻³⁶. In the HS region, on the other hand, two prominent drops of MIM-Im signals appear at around $V_{bg} \sim -2.1$ V and +1.8 V. On the hole-doping side, given the threshold voltage ~ -0.7 V for injecting holes into the WSe₂ layer, the insulating state corresponds to a filling factor $n/n_0 = -1$, i.e. one hole per moiré unit cell. The results are also consistent with the ODRC data (Fig. 1d) and previous investigations^{17,18}. The difference in the voltage values is because the ODRC measurements use the top gate with the top hBN thickness of 11 nm and the MIM measurements use the bottom gate with the bottom hBN thickness of 16 nm.

The insulating state with electron doping, however, has not yet been observed before. Given the ~ 0.3 V threshold voltage for injecting electrons, the observed insulating state at V_{bg} ~ 1.8 V corresponds to filling factor $n/n_0 = +1$, i.e. one electron per moiré unit cell. The fact that both WSe₂ and WS₂ are turned on at this threshold voltage suggests that the gate-induced electrons are located in both layers. Interestingly, while the two monolayer regions display comparable MIM-Im signals in the ambipolar FET curves, the overall MIM signal level on the electron-doped side is considerably lower than that on the hole-doped side, indicative of a large intrinsic resistance of the former. Such a property may lead to large contact resistance, which represents a big challenge for conventional transport measurements to access the electron side of WSe₂/WS₂ moiré superlattices at low doping and low temperatures. Further experiments are needed to examine this hypothesis. We emphasize that the requirement of good Ohmic contacts is much less stringent for the MIM measurements, which enables the observation of Mott states on both electron and hole sides. The Mott states persist up to ~ 150 K and eventually vanish at 295 K. A rough estimate of

the thermal activation gap of the Mott state is thus $10 \sim 20$ meV, consistent with the earlier reports^{17,18}.



FIG. 3. (a) Topographic image of the WSe₂/WS₂ device taken by the tuning-fork feedback. The WSe₂, WS₂, and top FLG regions are labeled by green, orange, and black dashed lines, respectively. The green, orange, and red stars mark the locations where the MIM curves in (d) are taken. (b) MIM-Im image at T = 24 K and $V_{bg} = 0$ V in the same area as (a). Inset: MIM-Im images in the blue dashed box in (b) taken at $V_{bg} = -2$ V. Scale bars in (a – b) are 2 µm. (c) MIM-Im signals at various locations and temperature. The two dash-dotted lines denote the charge neutral points, -0.7 V for holes in WSe₂ and +0.3 V for electrons in WS₂. The shaded areas correspond to the Mott insulating states at $n/n_0 = \pm 1$. The data at 295K HS is scaled by 0.2 for compact visualization.

Finally, we briefly discuss the spatial variation of the Mott insulating state in the moiré superlattice. Figs. 4a and 4b show the close-up AFM and MIM-Im images near the HS region at T = 24 K and $V_{bg} = -2$ V. In addition to the surface impurities visible from the topography, inhomogeneous local conductivity is clearly observed in the MIM image. In Fig. 4c, the MIM-Im signals when V_{bg} is swept from -2.7 V to 2.7 V are plotted for the three points labeled in Fig. 4b. The dips for $n/n_0 = \pm 1$, although present in all curves, differ significantly in their strengths and positions with respect to V_{bg} . The electrical inhomogeneity is indicative of spatial disorder in the correlated insulating state, which may be caused by strains, defects, density inhomogeneity from

electrostatic gating, and local variation of the twist angle. Future improvement on the sample uniformity is thus critical for in-depth understanding of correlation physics in 2D moiré superlattices.



FIG. 4. (a) Topography and (b) MIM-Im images at $V_{bg} = -2$ V for a close-up view in the heterostructure region. (c) MIM-Im signals at three different locations labeled in (a) as a function of the back-gate voltage. The positions of $n/n_0 = \pm 1$ are indicated by arrows for each curve.

In summary, we report the near-field microwave imaging of correlated states in semiconducting TMD hetero-bilayer moiré superlattices. The ability to probe local conductivity in buried structures allows us to observe the Mott insulating phases with both hole and electron doping at temperatures up to 150 K. The nanoscale microwave images reveal substantial spatial inhomogeneity in the correlated states. Our work provides a guideline for improving the material quality towards novel electronic states in 2D moiré systems.

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References

- J. M. B. Lopes dos Santos, N. M. R. Peres, A. H. Castro Neto, *Phys. Rev. Lett.* 99, 256802 (2007).
- R. Bistritzer, A. H. MacDonald, Proc. Natl. Acad. Sci. U.S.A. 108 (30), 12233-12237 (2011).
- M. Yankowitz, J. Xue, D. Cormode, J. D. Sanchez-Yamagishi, K. Watanabe, T. Taniguchi,
 P. Jarillo-Herrero, P. Jacquod, B. J. LeRoy, *Nat. Phys.* 8, 382–386 (2012).
- Y. Cao, V. Fatemi, A. Demir, S. Fang, S. L. Tomarken, J. Y. Luo, J. D. Sanchez-Yamagishi, K. Watanabe, T. Taniguchi, E. Kaxiras, R. C. Ashoori, P. Jarillo-Herrero, *Nature* 556, 80– 84 (2018).
- 5. Y. Cao, V. Fatemi, S. Fang, K. Watanabe, T. Taniguchi, E. Kaxiras, P. Jarillo-Herrero, *Nature* **556**, 43–50 (2018).
- G. Chen, L. Jiang, S. Wu, B. Lyu, H. Li, B. L. Chittari, K. Watanabe, T. Taniguchi, Z. Shi, J. Jung, Y. Zhang, F. Wang, *Nat. Phys.* 15, 237-241 (2019).
- G. Chen, A. L. Sharpe, P. Gallagher, I. T. Rosen, E. J. Fox, L. Jiang, B. Lyu, H. Li, K. Watanabe, T. Taniguchi, J. Jung, Z. Shi, D. Goldhaber-Gordon, Y. Zhang, F. Wang, *Nature* 572, 215-219 (2019).
- X. Lu, P. Stepanov, W. Yang, M. Xie, M. A. Aamir, I. Das, C. Urgell, K. Watanabe, T. Taniguchi, G. Zhang, A. Bachtold, A. H. MacDonald, D. K. Efetov, *Nature* 574, 653–657 (2019).
- M. Yankowitz, S. Chen, H. Polshyn, Y. Zhang, K. Watanabe, T. Taniguchi, D. Graf, A. F. Young, C. R. Dean, *Science* 363 (6431), 1059-1064 (2019).
- A. L. Sharpe, E. J. Fox, A. W. Barnard, J. Finney, K. Watanabe, T. Taniguchi, M. A. Kastner, D. Goldhaber-Gordon, *Science* 365 (6453) 605-608 (2019).

- 11. G. Chen, A. L. Sharpe, E. J. Fox, Y. H. Zhang, S. Wang, L. Jiang, B. Lyu, H. Li, K. Watanabe, T. Taniguchi, Z. Shi, T Senthil, D. Goldhaber-Gordon, Y. Zhang, F. Wang, *Nature* 579, 56-61 (2020).
- 12. M. Serlin, C. L. Tschirhart, H. Polshyn, Y. Zhang, J. Zhu, K. Watanabe, T. Taniguchi, L. Balents, A. F. Young, *Science* 367 (6480), 900-903 (2020).
- 13. F. Wu, T. Lovorn, E. Tutuc, A. H. MacDonald, Phys. Rev. Lett. 121, 026402 (2018).
- 14. Hubbard, J., Proc. R. Soc. Lond. A 276, 238–257 (1963).
- A. Singha, M. Gibertini, B. Karmakar, S. Yuan, M. Polini, G. Vignale, M. I. Katsnelson,
 A. Pinczuk, L. N. Pfeiffer, K. W. West, V. Pellegrini, *Science* 332 (6034) 1176-1179 (2011).
- L. Wang, E. Shih, A. Ghiotto, L. Xian, D. A. Rhodes, C. Tan, M. Claassen, D. M. Kennes, Y. Bai, B. Kim, K. Watanabe, T. Taniguchi, X. Zhu, J. Hone, A. Rubio, A. Pasupathy, C. R. Dean, *Nat. Mater.*, (2020). <u>https://www.nature.com/articles/s41563-020-0708-6</u>
- 17. Y. Tang, L. Li, T. Li, Y. Xu, S. Liu, K. Barmak, K. Watanabe, T. Taniguchi, A. H. MacDonald, J. Shan, K. F. Mak, *Nature* **579** (7799) 353-358 (2020).
- E. C. Regan, D. Wang, C. Jin, M. I. B. Utama, B. Gao, X. Wei, S. Zhao, W. Zhao, Z. Zhang,
 K. Yumigeta, M. Blei, J. D. Carlström, K. Watanabe, T. Taniguchi, S. Tongay, M.
 Crommie, A. Zettl, F. Wang, *Nature* 579 (7799) 359-363 (2020)
- 19. H. Pan, F. Wu, S. D. Sarma, arXiv:2004.04168 (2020).
- H. Yoo, R. Engelke, S. Carr, S. Fang, K. Zhang, P. Cazeaux, S. H. Sung, R. Hovden, A. W. Tsen, T. Taniguchi, K. Watanabe, G. Yi, M. Kim, M. Luskin, E. B. Tadmor, E. Kaxiras, P. Kim, *Nat. Mater.* 18, 448–453 (2019).
- M. R. Rosenberger, H. J. Chuang, M. Phillips, V. P. Oleshko, K. M. McCreary, S. V. Sivaram, C. S. Hellberg, B. T. Jonker, ACS Nano 14 (4), 4550–4558 (2020).
- A. Weston, Y. Zou, V. Enaldiev, A. Summerfield, N. Clark, V. Zólyomi, A. Graham, C. Yelgel, S. Magorrian, M. Zhou, J. Zultak, D. Hopkinson, A. Barinov, T. H. Bointon, A. Kretinin, N. R. Wilson, P. H. Beton, V. I. Fal'ko, S. J. Haigh, R. Gorbachev, *Nat. Nanotech.* (2020). <u>https://doi.org/10.1038/s41565-020-0682-9</u>
- 23. V. V. Enaldiev, V. Zólyomi, C. Yelgel, S. J. Magorrian, and V. I. Fal'ko, *Phys. Rev. Lett.*124, 206101 (2020).

- L. J. McGilly, A. Kerelsky, N. R. Finney, K. Shapovalov, E.-M. Shih, A. Ghiotto, Y. Zeng, S. L. Moore, W. Wu, Y. Bai, K. Watanabe, T. Taniguchi, M. Stengel, L. Zhou, J. Hone, X.-Y. Zhu, D. N. Basov, C. Dean, C. E. Dreyer, A. N. Pasupathy, *Nat. Nanotech.* (2020). https://www.nature.com/articles/s41565-020-0708-3
- C. Jin, E. C. Regan, A. Yan, M. I. B. Utama, D. Wang, S. Zhao, Y. Qin, S. Yang, Z. Zheng,
 S. Shi, K. Watanabe, T. Taniguchi, S. Tongay, A. Zettl, F. Wang, *Nature* 567 (7746), 76-80 (2019).
- 26. K. Lai, W. Kundhikanjana, M. Kelly, and Z. X. Shen, Rev. Sci. Instrum. 79, 063703 (2008).
- 27. K. Lai, H. Peng, W. Kundhikanjana, D. T. Schoen, C. Xie, S. Meister, Y. Cui, M. A. Kelly,
 Z. X. Shen, *Nano Lett.* 9 (3) 1265-1269 (2009).
- D. Wu, X. Li, L. Luan, X. Wu, W. Li, M. N. Yogeesh, R. Ghosh, Z. Chu, D. Akinwande,
 Q. Niu, K. Lai, *Proc. Natl. Acad. Sci.* 113 (31) 8583-8588 (2016).
- 29. Z. Chu, L. Zheng, K. Lai, Annu. Rev. Mater. Res. 50: 105-130 (2020).
- 30. Z. Chu, C. Wang, J. Quan, C. Zhang, C. Lei, A. Han, X. Ma, H. Tang, D. Abeysinghe, M. Staab, X. Zhang, A. H MacDonald, V. Tung, X. Li, C. Shih, K. Lai, *Proc. Natl. Acad. Sci. U.S.A.* **117** (25), 13908-13913 (2020).
- 31. Y. Cui, E. Y. Ma, Z. X. Shen, Rev. Sci. Instrum. 87 (6) 063711 (2016).
- X. Wu, Z. Hao, D. Wu, L. Zheng, Z. Jiang, V. Ganesan, Y. Wang, K. Lai, *Rev. Sci. Instrum.* 89 (4) 043704 (2018).
- 33. D. Braga, I. G. Lezama, H. Berger, A. F. Morpurgo, Nano Lett. 12, 10, 5218–5223 (2012).
- 34. B. W. H. Baugher, H. O. H. Churchill, Y. Yang and P. Jarillo-Herrero, *Nat. Nanotech.* 9, 262–267(2014).
- 35. Y. J. Zhang, T. Oka1, R. Suzuki, J. T. Ye, Y. Iwasa, Science 344 (6185), 725-728 (2014).
- D. Ovchinnikov, A. Allain, Y. Huang, D. Dumcenco, A. Kis, ACS Nano 8, 8174–8181 (2014).

S1. Fabrication details of the WSe₂/WS₂ moiré superlattices device.

The WSe₂/WS₂ heterostructure devices were fabricated by using a dry-transfer method with a polyethylene terephthalate (PET) stamp^[S1]. First, we exfoliated and transferred the TMD monolayers, few-layer graphene and thin hBN onto Si substrates with 90 nm SiO₂. Secondly, a PET stamp was used to sequentially pick up the few-layer graphene top gate, top hBN flake, the WSe₂ monolayer, the WS₂ monolayer, the few-layer graphene contact, the bottom hBN flake and the few-layer graphene back gate. Before picking up WS₂, the PET stamp was reoriented to ensure a near-60° angle between the WSe₂ and WS₂ flakes. All the layers were then stamped onto a clean SiO₂/Si substrate. The PET and samples were heated to 60 °C during the pick-up and to 130 °C for the stamping process. Finally, the PET was dissolved in dichloromethane overnight at room temperature. The gold contacts (~75 nm with a ~5-nm-thick chromium adhesion layer) to the few-layer graphene flakes were made using electron-beam lithography and electron-beam evaporation.

S2. Determination of the twist angle between monolayer WSe₂ and WS₂ flakes.

We determined the twist angle (60.0 ± 0.3 degrees) between WSe₂ and WS₂ flakes by performing polarization dependent second harmonic generation (SHG) measurements on both the TMD monolayers and heterostructure regions in the device^{[S2], [S3]} (Fig. S2). The absence of SHG signal on the heterostructure region indicates that the twist angle is close to 60 degrees, rather than 0 degree.



Fig. S2. Polarization-dependent SHG signal on monolayer WSe_2 (red circles) and WS_2 (black circles) of the device and corresponding fittings (red and black curves). The twist angle between the WSe_2 and WS_2 flakes is 60.0 ± 0.3 degrees.

S3. Back gate dependent absorption spectra.



Fig. S3. Absorption spectra of the back-gate-only region (Region II in Fig. 1b in the main text) at 10 K while tuning the back-gate voltage from -2 V to 2 V with 0.1 V increment.

S4. ODRC measurements at 10 K.

The ODRC measurements on the WSe₂/WS₂ moiré superlattice were performed following the experimental description in reference [S4]. The superlattice devices include a local top gate: region I is covered by the gate, and region II is not. The few-layer-graphene top gate carries both d.c. voltage (V_{tg}) and a.c. excitation voltage ($\Delta \tilde{V}$). The d.c. voltage is used to continuously control the carrier doping in region I, while a small (10 mV) a.c. voltage with high excitation frequency (w) is applied to redistribute the charge between region I and region II without any changes on the total charge. The charge redistribution depends on the quantum capacitance (C_Q) and resistance (R) of the moiré superlattice in region I, and leads to a change of carrier concentration ($\Delta \tilde{n}$) in region II, which can be detected optically. We directly measured the change in optical contrast at region II, ΔOC , using a laser probe (1.70 eV) resonant with the lowest energy WSe₂ A exciton peak. As shown in Fig. S4a, the relationship between $\Delta \tilde{V}$, $\Delta \tilde{n}$ and ΔOC can be described by an effective circuit model (Eq. S1)^[S4].

$$\Delta OC = \alpha \Delta \tilde{n} = \frac{\alpha}{A_2 e} \Delta \tilde{V} \frac{C_{1t}}{C_{1t} + C_{1b}} \frac{1}{\frac{1}{C_{1t} + C_{1b}} + \frac{1}{C_{2b}} + \frac{1}{C_0} + iwR}$$
(S1)

Here, α is the optical detection responsivity in region II, C_{1t} and C_{1b} are the geometric capacitances between the TMD and the top and bottom gates in region I respectively. C_{2b} is the TMD-bottom gate capacitance in region II. These geometric capacitances C_i (i = 1t, 1b, 2b) are set by $C_i = \varepsilon_0 \varepsilon_r A_i/d_i$, where ε_r is the dielectric constant (~ 4.2 ± 0.4) of the gate dielectric, i.e. hBN, A_i and d_i are the relevant capacitor area and separation, respectively.

Besides the result shown in Figure 1d in the main text, Fig. S4b-c show two additional rounds of measured ODRC signals as a function of the top-gate voltage (V_{tg}) in region I at various excitation frequencies. The locations of the probe laser spot might have slightly shifted between the three rounds of measurements. When $V_{tg} > -0.3$ V, the heterostructure is charge neutral and the ODRC signal is negligibly small. When $V_{tg} < -0.3$ V, hole doping starts in region I and charge redistribution occurs, leading to a large increase in the ODRC signal. Mott insulating states are consistently observed at $V_{tg} \sim -1.37$ V in all ODRC measurements.



Fig. S4. (a)The diagram of the effective RC circuit for ODRC measurements. (b-c) Two additional ODRC measurements at different excitation frequencies. The hole-doped Mott insulating states appear in all measurements.

S5. 2D finite element analysis (FEA).

We performed finite-element analysis^[S5] to simulate the MIM response to 2D sheet conductance using the commercial software COMSLO 4.4. Fig. S5a shows the schematic of tip-sample geometry, where the tip is on top of the monolayer WS₂. The shape of the tip is defined by the following parameters: diameter d = 100 nm, half-cone angle $\theta = 10^{\circ}$. The parameters of the device are as follows. The thicknesses of top and bottom hBN are 11 nm and 16 nm, respectively, and the dielectric constant of hBN is 4.2 ^[S4]. The WS₂ monolayer is 1 nm in thickness, with a dielectric constant of $3.5^{[S6]}$. The few-layer bottom graphene layer is ~ 4 nm thick, and its dielectric constant at GHz frequency is ~ 4 ^[S7]. The conductivity of the few-layer graphene is on the order of 10^4 S/m. The substrate is Si with 90 nm SiO₂ whose dielectric constant is ~ 3.9 ^[S8].

The simulated MIM signals as a function of the sheet conductance of WS₂ are presented in Fig. 2b in the main text. Fig. S5b shows the quasi-static potential distribution at $\sigma_{WS_2} = 10^{-9}$ S·sq and 10^{-5} S·sq. Without any doping, the WS₂ layer is highly resistive, and there is virtually no charge screening effect from the WS₂ layer. In contrast, when the WS₂ layer is doped and becomes very conducting (10^{-5} S·sq), the electric field is effectively screened by the WS₂ layer.



Fig. S5. (a) Schematic of tip-sample geometry for the FEA simulation. (b) Quasi-static potential distributions at $\sigma_{WS_2} = 10^{-9} \text{ S} \cdot \text{sq}$ (left) and $10^{-5} \text{ S} \cdot \text{sq}$ (right).

S6. A complete set of the MIM data.



Fig. S6. (a) Topographic image of the TMD device, where the black dashed rectangle highlights the scanning area in (b,c). The red, green, and orange stars marked the locations where MIM curves (shown in (d)) were measured for heterostructure (HS), WSe₂ and WS₂ respectively. (b) MIM-Im and MIM-Re images were taken at $V_{bg} = -2V$. (c) MIM signals as a function of V_{bg} at the HS, WSe₂, and WS₂ regions marked in (a) at 24K. The MIM curves for three additional temperatures at 35K, 150K, and 295K are also shown for HS (red star). The dark red lines are the corresponding MIM-Re signals. Although there is minimal MIM-Re signal when the sample is either very conducting or insulating, the dips in MIM-Re signals indeed correspond to the correlated states. The shaded areas indicate the Mott insulating states at $n/n_0 = \pm 1$. The dash-dotted lines denote the charge neutral points, -0.7 V for the holes side and +0.3 V for the electrons side.

S7. Correlated insulating states in a near-zero twist angle WSe₂/WS₂ device.

We investigated another WSe₂/WS₂ moiré superlattice device at 20K, where the twist angle is near zero-degree. Other parameters of the device, such as the thickness of hBN, FLG, are similar to the one presented in the main text. Fig. S7a shows the optical microscope image of the device with a relatively large field of view, where the FLG back gate and contact are marked. Fig. S7b shows the zoom-in optical picture of the TMD moiré heterostructure, which is highlighted by the white dashed rectangle in (a). The absorption spectrum at zero gate voltage at 10 K (Fig. S7c) shows three prominent peaks come from the splitting of the WSe₂ A exciton, which demonstrates the presence of the moiré potential. Fig. S7d shows the measured MIM-Re signals as a function of the back-gate voltage and filling factors at the point marked by the red star in (Fig. S7b). The dips in MIM-Re signals suggest the insulating states. Besides the Mott states at half filling ($n/n_0 = \pm 1$) on both electron and hole sides, we also observed insulating behaviors at full filling ($n/n_0 = \pm 2$) of the moiré band, and at -2/3 filling on the hole side. MIM-Im signals are too noisy and were not recorded during the measurements.



Fig. S7. (a) Optical microscope image of the device. (b) Zoom-in view of the TMD moiré heterostructure outlined by the white rectangle in (a). The FLG, WSe₂, and WS₂ regions are

indicated by white, green, and orange contours. (c) Absorption spectrum at zero back-gate voltage. The dashed lines indicate the peaks in reflectance due to the splitting of the WSe₂ A exciton. (d) MIM-Re signals as a function of the back-gate voltage and filling factors measured at the point marked by the red star in (b). The MIM measurement was performed at 20 K.

References:

[S1] L. Wang, I. Meric, P. Y. Huang, Q. Gao, Y. Gao, H. Tran, T. Taniguchi, K. Watanabe, L.
M. Campos, D. A. Muller, J. Guo, P. Kim, J. Hone, K. L. Shepard, C. R. Dean, *Science* 342, 614–617 (2013).

[S2] N. Kumar, S. Najmaei, Q. Cui, F. Ceballos, P. M. Ajayan, J. Lou, H. Zhao, *Phys. Rev. B* 87, 161403 (2013).

[S3] Y. Li, Y. Rao, K. F. Mak, Y. You, S. Wang, C. R. Dean, and T. F. Heinz, *Nano Lett.* **13**, 3329–3333 (2013).

[S4] E. C. Regan, D. Wang, C. Jin, M. I. B. Utama, B. Gao, X. Wei, S. Zhao, W. Zhao, Z. Zhang,
K. Yumigeta, M. Blei, J. D. Carlström, K. Watanabe, T. Taniguchi, S. Tongay, M. Crommie, A.
Zettl, F. Wang, *Nature* 579 (7799) 359-363 (2020).

[S5] K. Lai, W. Kundhikanjana, M. Kelly, Z. X. Shen, Rev. Sci. Instrum. 79, 063703 (2008).

[S6] A. Laturia, M. L. Van de Put, W. G. Vandenberghe, npj 2D Mater. Appl. 2, 6 (2018).

[S7] S. Bellucci, A. Maffucci, S. Maksimenko, F. Micciulla, M. D. Migliore, A. Paddubskaya,

D. Pinchera, F. Schettino, *Materials* 11 (12), 2519 (2018).

[S8] K. Murase, Japanese Journal of Applied Physics **33** (1) 3A (1994).